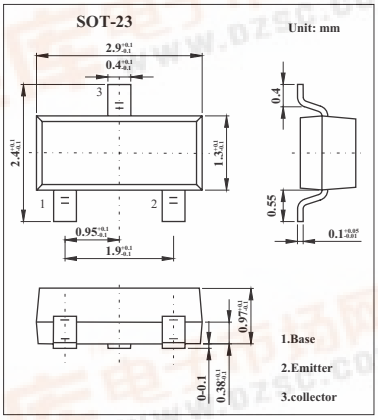
PNP Epitaxial Planar Silicon Transistors

2SB1527



Features

- Low saturation voltage.
- Contains a diode between collector and emitter.
- Contains a bias resistor between base and emitter.
- Large current capacity.
- Compact package making it easy to realize highdensity, small-sized hybrid ICs.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-15	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-0.8	A
Collector current (pulse)	I_{CP}	-2	A
Collector dissipation	P_C	200	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = -15V , I_E = 0			-1	μA
DC current Gain	h_{FE}	V_{CE} = -2V , I_C = -0.5A	70			
Gain bandwidth product	f_T	V_{CE} = -2V , I_C = -0.5A		250		MHz
Output capacitance	C_{ob}	V_{CB} = -10V , f = 1MHz		30		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -500mA , I_B = -10mA		-0.2	-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = -500mA , I_B = -10mA		-.095	-1.3	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	I_C = -10μA , I_E = 0	-20			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1mA , R_{BE} = ∞	-15			V
Diode forward voltage	V_F	I_F=-0.5A			-1.5	V
Base-emitter resistance	R_{BE}			1		KΩ

Marking

Marking	NS